

Appl. No. 10/605,585
Response dated April 26, 2005
Reply to Office Action of Jan. 26, 2005

The following listing of claims will replace all prior versions, and listings, of claims in the application.

LISTING OF CLAIMS:

Claim 1 (currently amended): A semiconductor device, comprising:
a semiconductor substrate main unit; and
a thin portion that is thinner than the main unit and formed such that a recessed portion is formed in the semiconductor substrate, the thin portion having at least one through hole formed therein;

wherein the main unit and the thin portion are comprised of the same semiconductor material; and

~~wherein~~ the thin portion is formed such that the etching rate thereof is slower than that of the main unit.

Claim 2 (original): The semiconductor device set forth in claim 1, wherein the thin portion and the main unit are formed to be unitary with each other.

Claim 3 (original): The semiconductor device set forth in claim 1, wherein a dopant is infused in the thin portion.

Claim 4 (original): The semiconductor device set forth in claim 1, wherein the thin portion is formed by means of a selective oxide film.

Claims 5-12 (cancelled)